

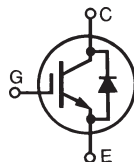
**GenX3™ 1200V  
IGBTs w/ Diode**
**IXGK55N120A3H1  
IXGX55N120A3H1**

$$V_{CES} = 1200V$$

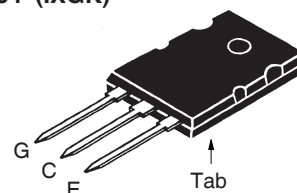
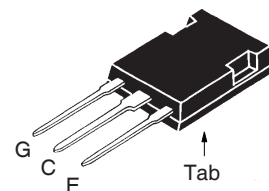
$$I_{C110} = 55A$$

$$V_{CE(sat)} \leq 2.3V$$

Ultra-Low-Vsat PT IGBTs for  
up to 3kHz Switching



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ ( Chip Capability )	125	A
$I_{C110}$	$T_C = 110^\circ C$	55	A
$I_{LRMS}$	$T_C = 25^\circ C$ (Lead RMS Limit)	120	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	400	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 3\Omega$ Clamped Inductive Load	$I_{CM} = 110$ @ $0.8 \cdot V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	460	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
$M_d$	Mounting Torque ( IXGK )	1.13/10	Nm/lb.in.
$F_C$	Mounting Force ( IXGX )	20..120/4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

**TO-264 (IXGK)**

**PLUS247™ (IXGX)**


G = Gate                      E = Emitter  
C = Collector                Tab = Collector

**Features**

- Optimized for Low Conduction Losses
- Anti-Parallel Ultra Fast Diode

**Advantages**

- High Power Density
- Low Gate Drive Requirement

**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 1mA$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ Note 1, $T_J = 125^\circ C$			100 $\mu A$ 2.0 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = I_{C110}$ , $V_{GE} = 15V$ , Note 2 $T_J = 125^\circ C$	1.85 1.90		2.3 V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = I_{C110}, V_{CE} = 10\text{V}$ , Note 2	30	45	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		4340	pF
$C_{oes}$			300	pF
$C_{res}$			115	pF
$Q_{g(on)}$	$I_C = I_{C110}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		185	nC
$Q_{ge}$			25	nC
$Q_{gc}$			75	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C110}, V_{GE} = 15\text{V}$		23	ns
$t_{ri}$			42	ns
$E_{on}$			5.1	mJ
$t_{d(off)}$	Note 3 $V_{CE} = 0.8 \cdot V_{CES}, R_G = 3\Omega$		365	ns
$t_{fi}$			282	ns
$E_{off}$			13.3	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C110}, V_{GE} = 15\text{V}$		24	ns
$t_{ri}$			46	ns
$E_{on}$			9.5	mJ
$t_{d(off)}$	Note 3 $V_{CE} = 0.8 \cdot V_{CES}, R_G = 3\Omega$		618	ns
$t_{fi}$			635	ns
$E_{off}$			29.0	mJ
$R_{thJC}$			0.27	$^\circ\text{C/W}$
$R_{thCK}$		0.15		$^\circ\text{C/W}$

### Reverse Diode (FRED)

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 60\text{A}, V_{GE} = 0\text{V}$ , Note 2 $T_J = 150^\circ\text{C}$	1.85	2.5	V
$t_{rr}$	$I_F = 60\text{A}, V_{GE} = 0\text{V}$ , $-di_F/dt = 350\text{A}/\mu\text{s}, V_R = 600\text{V}, T_J = 100^\circ\text{C}$		200	ns
$I_{RM}$			24.6	A
$R_{thJC}$			0.42	$^\circ\text{C/W}$

### Notes:

1. Part must be heatsunk for high-temp  $I_{ces}$  measurement.
2. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
3. Switching times & energy losses may increase for higher  $V_{CE}$  (Clamp),  $T_J$  or  $R_G$ .

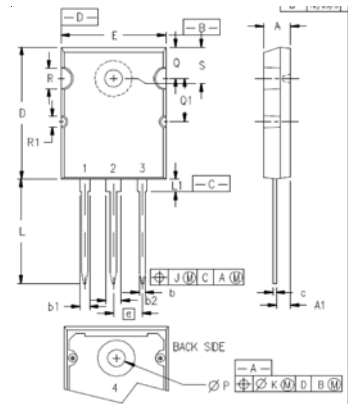
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

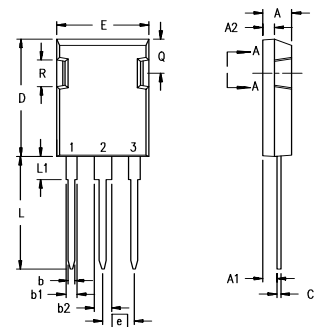
### TO-264 (IXGK) Outline



Terminals: 1 = Gate  
2 = Collector  
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

### PLUS 247™ (IXGX) Outline



Terminals: 1 = Gate  
2 = Collector  
3 = Emitter

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190